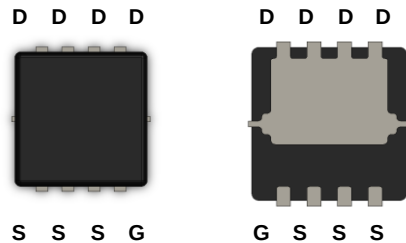


General Description

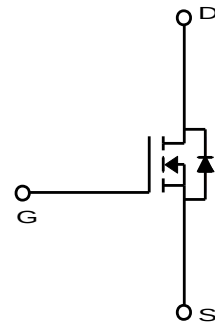
The MDV10N1K1 uses advanced MagnaChip's MOSFET Technology, which provides high performance in on-state resistance, fast switching performance and excellent quality. MDV10N1K1 is suitable device for DC to DC converter, Load Switch and general purpose applications.

Features

- $V_{DS} = 100V$
- $I_D = 12.3A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} (MAX) < 110m\Omega$ @ $V_{GS} = 10V$
 $< 116m\Omega$ @ $V_{GS} = 6.0V$
- 100% UIL Tested



PDFN33



Absolute Maximum Ratings ($T_c = 25^\circ C$)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		V_{DSS}	100	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current ⁽¹⁾	$T_c = 25^\circ C$	I_D	12.3	A
	$T_c = 70^\circ C$		9.9	
Pulsed Drain Current ⁽²⁾		I_{DM}	49	A
Power Dissipation	$T_c = 25^\circ C$	P_D	36.8	W
	$T_c = 70^\circ C$		23.5	
Single Pulse Avalanche Energy ⁽³⁾		E_{AS}	14	mJ
Junction and Storage Temperature Range		T_J, T_{stg}	-55~150	$^\circ C$

Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	36	$^\circ C/W$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	3.4	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDV10N1K1URH	-55~150°C	PDFN33	Tape & Reel	Halogen Free

Electrical Characteristics (T_J = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	100	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	2.0	3.0	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V	-	-	1	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	±0.1	
Drain-Source ON Resistance	R _{DS(ON)}	V _{GS} = 10V, I _D = 10A	-	90	110	mΩ
		V _{GS} = 6.0V, I _D = 10A	-	96	116	
Forward Transconductance	g _{fs}	V _{DS} = 10V, I _D = 10A	-	17	-	S
Dynamic Characteristics						
Total Gate Charge	Q _{g(10V)}	V _{DS} = 50V, I _D = 10A, V _{GS} = 10V	-	9.0	-	nC
Gate-Source Charge	Q _{gs}		-	2.4	-	
Gate-Drain Charge	Q _{gd}		-	1.5	-	
Input Capacitance	C _{iss}	V _{DS} = 40V, V _{GS} = 0V, f = 1.0MHz	-	450	-	pF
Reverse Transfer Capacitance	C _{rss}		-	20	-	
Output Capacitance	C _{oss}		-	50	-	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 50V, I _D = 10A , R _G = 3.0Ω	-	6.6	-	ns
Rise Time	t _r		-	10.1	-	
Turn-Off Delay Time	t _{d(off)}		-	17.0	-	
Fall Time	t _f		-	6.5	-	
Drain-Source Body Diode Characteristics						
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 10A, V _{GS} = 0V	-	0.75	1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 10A, dI/dt = 100A/μs	-	42.0	-	ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	69.0	-	nC

Note :

1. Surface mounted FR-4 board by JEDEC (jesd51-7)
2. Pulse width limited by T_{Jmax}
3. E_{AS} is tested at starting T_J = 25°C, L = 1.0mH, I_{AS} = 5.3A, V_{DD} = 50V, V_{GS} = 10V

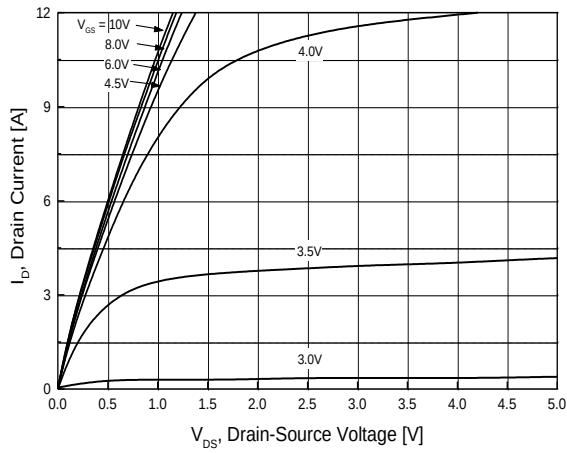


Fig.1 On-Region Characteristics

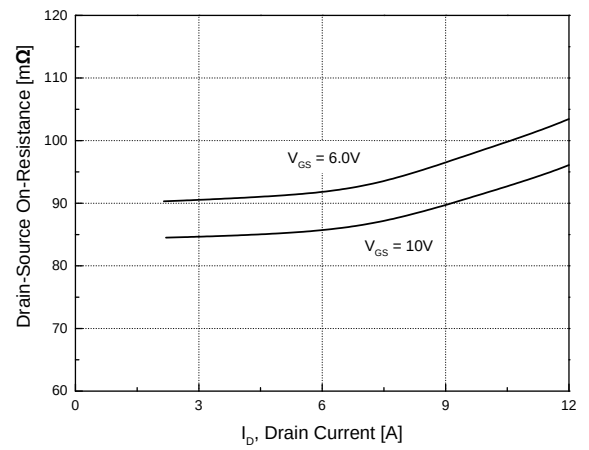


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

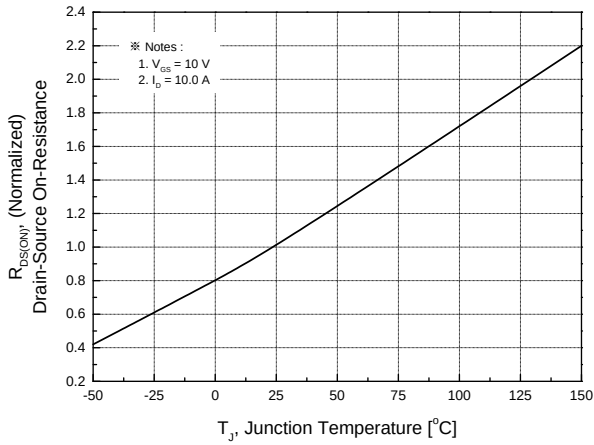


Fig.3 On-Resistance Variation with Temperature

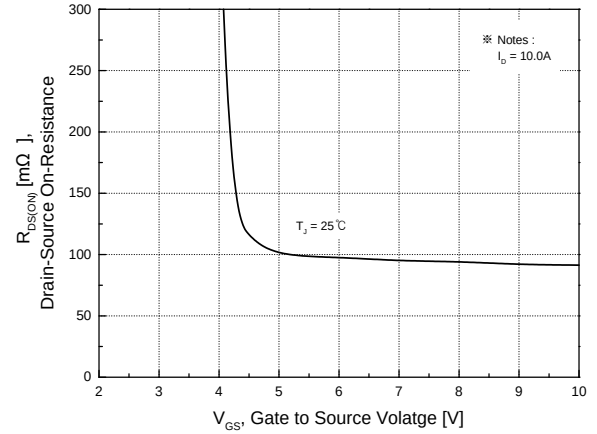


Fig.4 On-Resistance Variation with Gate to Source Voltage

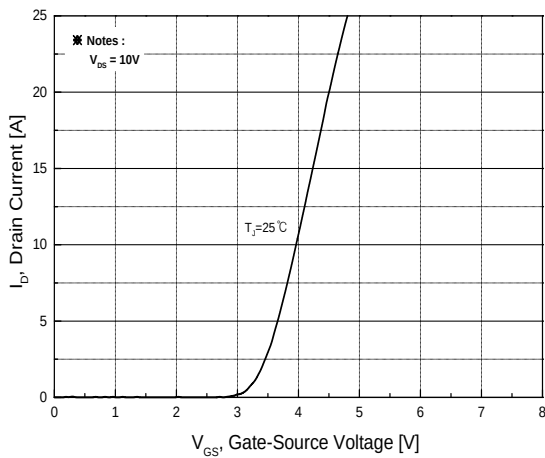


Fig.5 Transfer Characteristics

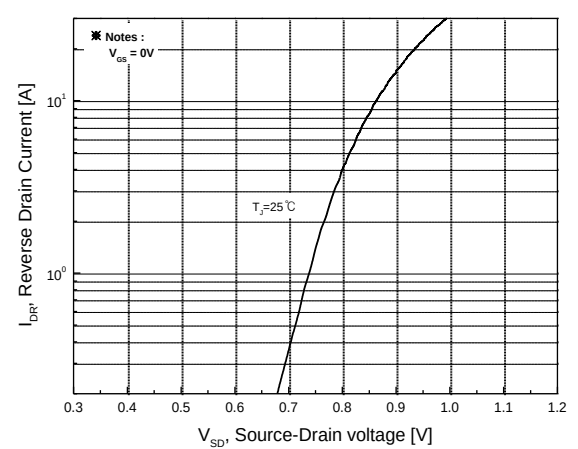
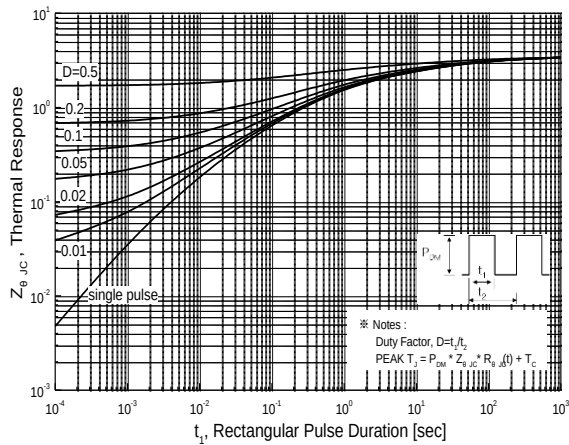
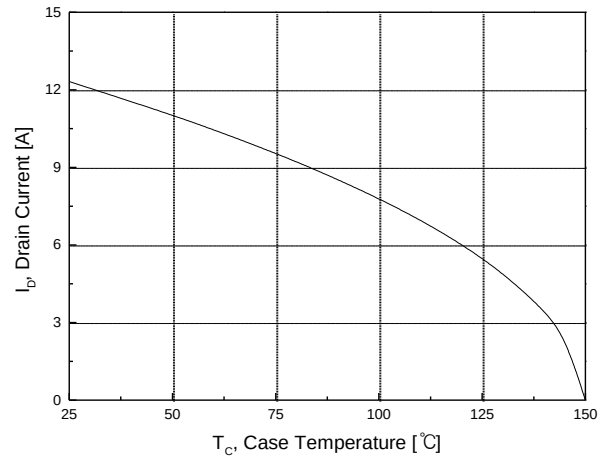
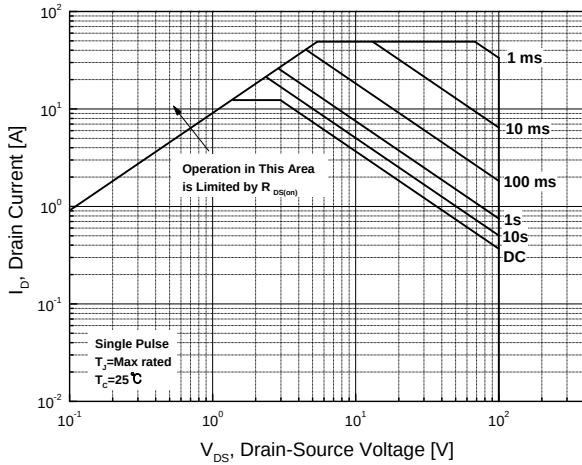
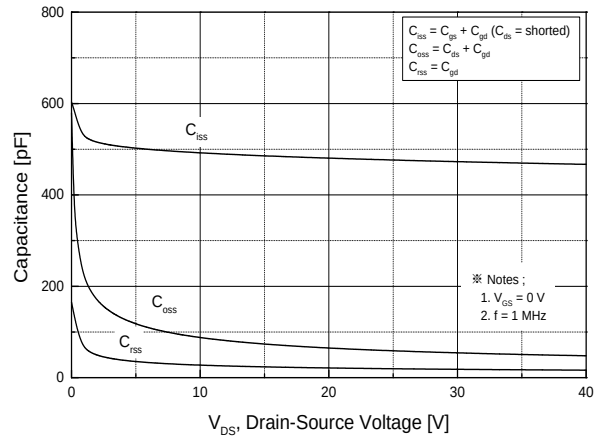
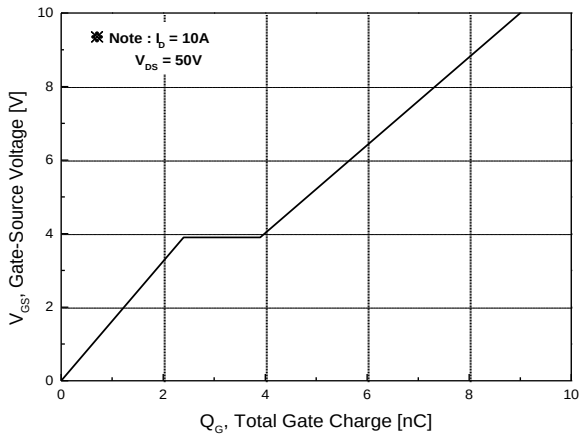


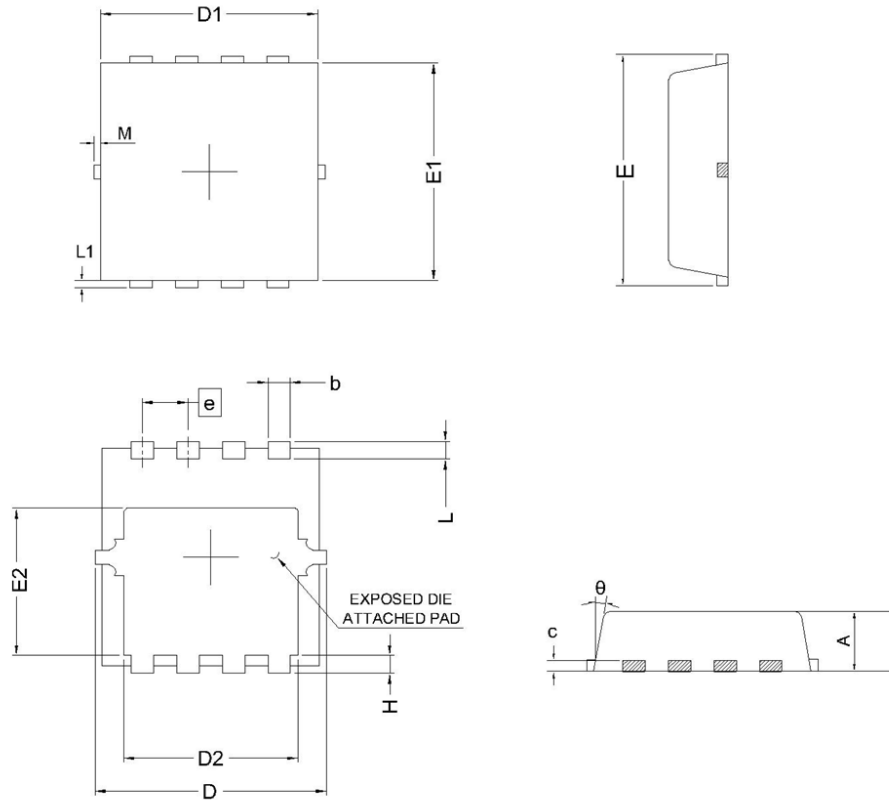
Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature



Package Dimension

PowerDFN33 (3.3x3.3mm)

Dimensions are in millimeters, unless otherwise specified



(Unit : mm)

	Min	Max
A	0.70	0.80
b	0.25	0.35
c	0.10	0.25
D	3.20	3.40
D1	3.00	3.20
D2	2.39	2.59
E	3.25	3.45
E1	3.00	3.20
E2	1.78	1.98
e	0.65 BSC	
L	0.30	0.50
L1	0.13 TYP.	
H	0.27	0.47
θ	0°	12°